

General Description

These P-Channel enhancement mode power field effect transistors use advanced trench technology and design to provide excellent RDS(ON) . This device is suitable for use as a load switch or in PWM applications.

Features

- Fast switching speed
- Lower On-resistance
- 100% EAS Guaranteed
- Simple Drive Requirement

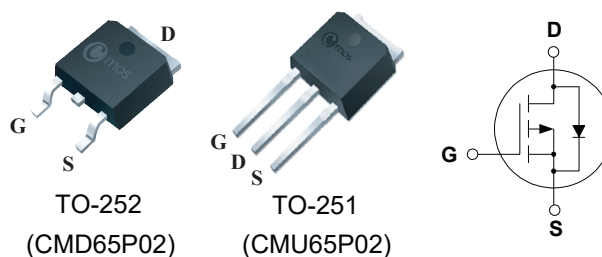
Product Summary

BVDSS	RDSON	ID
-20V	10.5mΩ	-65A

Applications

- DC-DC Converters
- Load Switches
- BLDC Motor driver

TO-252 / 251 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	-20	V
V _{GS}	Gate-Source Voltage	±12	V
I _D @T _C =25°C	Continuous Drain Current	-65	A
I _{DM}	Pulsed Drain Current	-260	A
EAS	Single Pulse Avalanche Energy ¹	112	mJ
P _D @T _C =25°C	Total Power Dissipation	60	W
T _{STG}	Storage Temperature Range	-55 to 150	°C
T _J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R _{θJA}	Junction-to-Ambient	---	62.5	°C/W
R _{θJC}	Junction-to-Case (Drain)	---	2.1	°C/W

Electrical Characteristics ($T_J=25^{\circ}\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DS}	Drain-Source Breakdown Voltage	$V_{GS}=0\text{V}$, $I_D=-250\mu\text{A}$	-20	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=-4.5\text{V}$, $I_D=-30\text{A}$	---	---	10.5	$\text{m}\Omega$
		$V_{GS}=-2.5\text{V}$, $I_D=-20\text{A}$	---	---	14.5	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=-250\mu\text{A}$	-0.5	---	-1.5	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=-16\text{V}$, $V_{GS}=0\text{V}$, $T_J=25^{\circ}\text{C}$	---	---	-1	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 12\text{V}$, $V_{DS}=0\text{V}$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=-10\text{V}$, $I_D=-10\text{A}$	---	22	---	S
R_g	Gate Resistance	$V_{DS}=0\text{V}$, $V_{GS}=0\text{V}$, $f=1\text{MHz}$	---	12.5	---	Ω
Q_g	Total Gate Charge	$V_{DD}=-15\text{V}$, $I_D=-10\text{A}$ $V_{GS}=-4.5\text{V}$	---	115	---	nC
Q_{gs}	Gate-Source Charge		---	7	---	
Q_{gd}	Gate-Drain Charge		---	20	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DS}=-10\text{V}$, $V_{GS}=-4.5\text{V}$, $R_{GS}=6\Omega$ $I_D=-1\text{A}$	---	25	---	ns
T_r	Rise Time		---	60	---	
$T_{d(off)}$	Turn-Off Delay Time		---	155	---	
T_f	Fall Time		---	65	---	
C_{iss}	Input Capacitance	$V_{DS}=-15\text{V}$, $V_{GS}=0\text{V}$, $f=1\text{MHz}$	---	3500	---	pF
C_{oss}	Output Capacitance		---	410	---	
C_{rss}	Reverse Transfer Capacitance		---	340	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	$V_G=V_D=0\text{V}$, Force Current	---	---	-65	A
I_{SM}	Pulsed Source Current		---	---	-260	A
V_{SD}	Diode Forward Voltage	$V_{GS}=0\text{V}$, $I_F=-20\text{A}$	---	---	-1.5	V

Note :

1.EAS condition: $T_J=25^{\circ}\text{C}$, $V_{DD}=-10\text{V}$, $V_{GS}=-10\text{V}$, $I_D=-15\text{A}$, $L=1\text{mH}$.

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Cmos reserves the right to improve product design ,functions and reliability without notice.

Typical Characteristics

